

#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 9)
30V	$1.0 \text{m}\Omega$ @ $V_{GS} = 10V$	100A
	1.6mΩ @ V <sub>GS</sub> = 4.5V	100A

#### **Features**

- 100% Unclamped Inductive Switching—Ensures More Reliable and Robust End Application
- Thermally Efficient Package-Cooler Running Applications
- High-Conversion Efficiency
- Low R<sub>DS(ON)</sub>—Minimizes On-State Losses
- <1.1mm Package Profile—Ideal for Thin Applications</li>
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

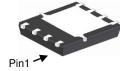
## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters
- Synchronous Rectification

#### PowerDI5060-8 (Type K)



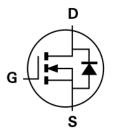


Top View

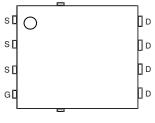
**Bottom View** 

### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish—Matte Tin Annealed Over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Internal Schematic



Top View Pin Configuration

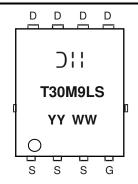
# Ordering Information (Note 4)

Part Number	Case	Packaging
DMT30M9LPS-13	PowerDI5060-8 (Type K)	2500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



T30M9LS = Product Type Marking Code
YYWW or YYWW = Date Code Marking
YY or YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)



# 

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	30	V	
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous-Drain Current, V <sub>GS</sub> = 10V (Notes 6 & 9)	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	100 100	А
Pulsed-Drain Current (380µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	400	Α
Continuous Body Diode Forward Current (Note 6)	T <sub>C</sub> = +25°C	I <sub>S</sub>	100	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	400	Α	
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	95.9	Α	
Avalanche Energy, L = 0.1mH		E <sub>AS</sub>	460	mJ

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\Theta JA}$	48	°C/W
Total Power Dissipation (Note 6)	$P_{D}$	113.6	W
Thermal Resistance, Junction to Case (Note 6)	R <sub>eJC</sub>	1.1	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

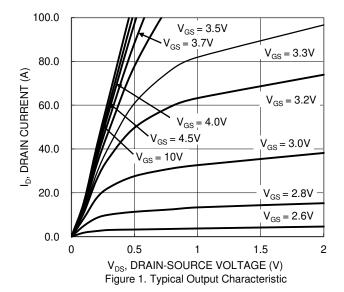
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30		_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	1	1	μΑ	$V_{DS} = 24V$ , $V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = +16V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.83	3	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	0.7	1.0	mΩ	$V_{GS} = 10V, I_D = 25A$	
Static Drain-Source On-nesistance	R <sub>DS(ON)</sub>	_	1.08	1.6	11122	$V_{GS} = 4.5V, I_D = 25A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.3	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		12,121	_		$V_{DS}$ = 20V, $V_{GS}$ = 0V, $f$ = 1MHz	
Output Capacitance	Coss	_	3325	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	128	_			
Gate Resistance	R <sub>G</sub>	_	3.57	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	160.5	_		V <sub>DD</sub> = 20V, I <sub>D</sub> = 50A	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qq	_	71.3	_	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	29.4	_	110		
Gate-Drain Charge	$Q_{qd}$	_	28.8	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	8.06	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{G} = 2.5\Omega$	
Turn-On Rise Time	t <sub>R</sub>		31.1	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>		121	_	ns		
Turn-Off Fall Time	t <sub>F</sub>		49.6	_			
Reverse Recovery Time	t <sub>RR</sub>		82.9	_	ns	1 50A di/dh 100A/	
Reverse Recovery Charge	Q <sub>RR</sub>	_	180.7	_	nC	$I_F = 50A$ , di/dt = 100A/ $\mu$ s	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper with thermal bias to bottom layer 1inch square copper plate.

- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.
- 9. Limited by package. Silicon chip capability is 304A at +25°C.







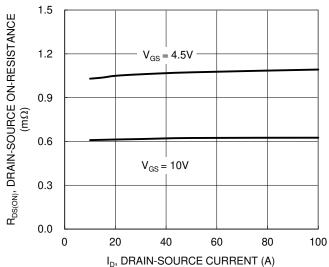


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

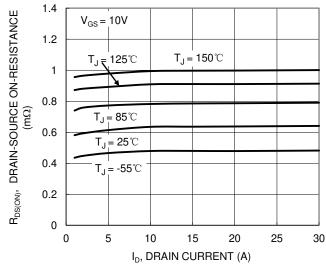
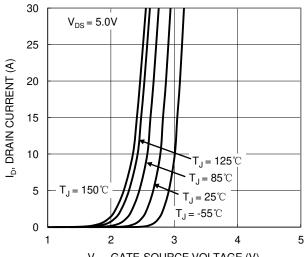


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



 $V_{\text{GS}}$ , GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

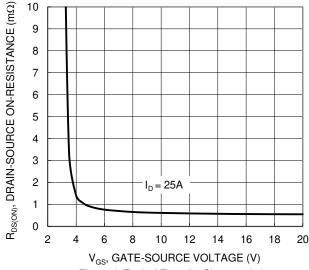


Figure 4. Typical Transfer Characteristic

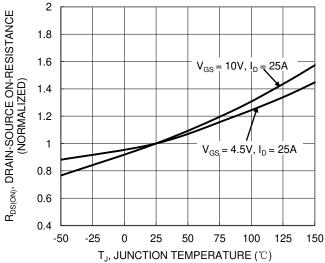


Figure 6. On-Resistance Variation with Temperature



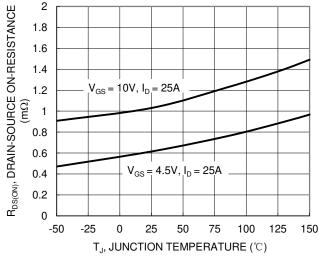


Figure 7. On-Resistance Variation with Temperature

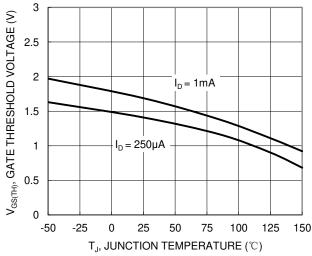


Figure 8. Gate Threshold Variation vs. Junction Temperature

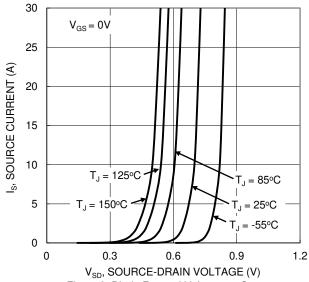
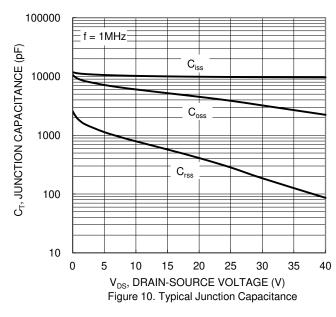
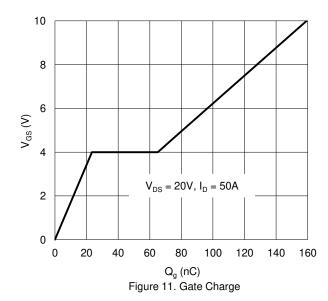


Figure 9. Diode Forward Voltage vs. Current





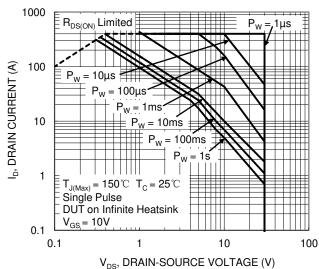


Figure 12. SOA, Safe Operation Area



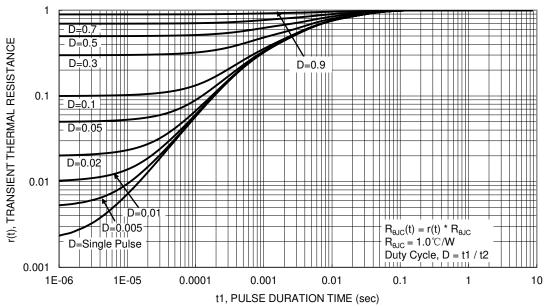


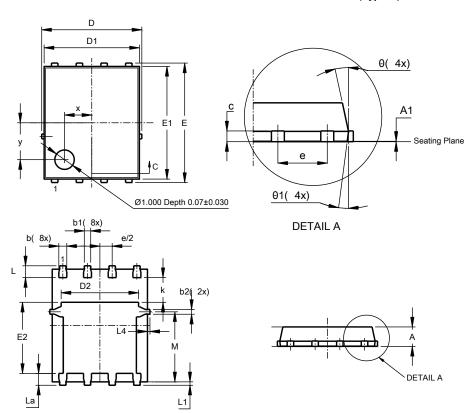
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type K)

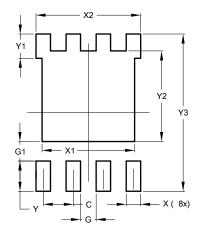


PowerDI5060-8 (Type K)					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5	.15 BS0	)		
D1	4.85	4.95	4.90		
D2	-	-	3.98		
Е	6.15 BSC				
E1	5.75	5.85	5.80		
E2	3.56	3.725	3.66		
е	1.27BSC				
k	-	-	1.27		
L	0.51	0.71	0.61		
La	0.51	0.675	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
М	3.50	3.71	3.605		
X	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type K)



Dimensions	value			
Dilliensions	(in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	3.910			
X2	4.420			
Υ	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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